



7N20Z

Power MOSFET

7A, 200V N-CHANNEL POWER MOSFET

DESCRIPTION

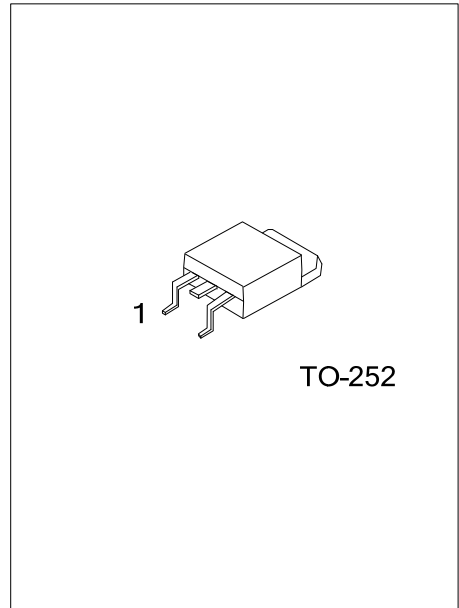
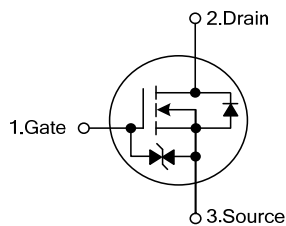
The UTC **7N20Z** is an N-Channel enhancement mode power MOSFET providing customers with excellent switching performance and minimum on-state resistance. This device can also withstand high energy pulse in the avalanche and the commutation mode.

The UTC **7N20Z** is generally applied in low voltage applications, such as DC motor controls, audio amplifiers and high efficiency switching DC/DC converters.

FEATURES

- * Low Gate Charge: 5.8nC (TYP.)
- * Low C_{RSS} : 10 pF (TYP.)
- * $R_{DS(ON)} = 0.58\Omega @ V_{GS} = 10 V$
- * Fast Switching
- * Improved dv/dt Capability

SYMBOL



ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|---------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 7N20ZL-TN3-R | 7N20ZG-TN3-R | TO-252 | G | D | S | Tape Reel |
| 7N20ZL-TN3-T | 7N20ZG-TN3-T | TO-252 | G | D | S | Tube |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|---|---|
| <p>7N20ZL-TN3-R</p> <p>(1)Packing Type (2)Package Type (3)Lead Free</p> | <p>(1) R: Tape Reel, T: Tube (2) TN3: TO-252 (3) G: Halogen Free, L:Lead Free</p> |
|---|---|

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---|------------------|------------|------|
| Drain -Source Voltage | V _{DSS} | 200 | V |
| Gate-Source Voltage | V _{GSS} | ±25 | V |
| Continuous Drain Current T _C =25°C | I _D | 7 | A |
| Pulsed Drain Current (Note 2) | I _{DM} | 28 | A |
| Single Pulsed Avalanche Energy (Note 3) | E _{AS} | 130 | mJ |
| Power Dissipation | P _D | 2.5 | W |
| Operating Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{STG} | -55 ~ +150 | °C |

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. L =26mH, I_{AS} =7A, V_{DD} =25V, R_G =25Ω Starting T_J =25°C

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|-----------------|---------|------|
| Junction to Ambient | θ _{JA} | 50 | °C/W |

Note: When mounted on the minimum pad size recommended (PCB Mount)

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

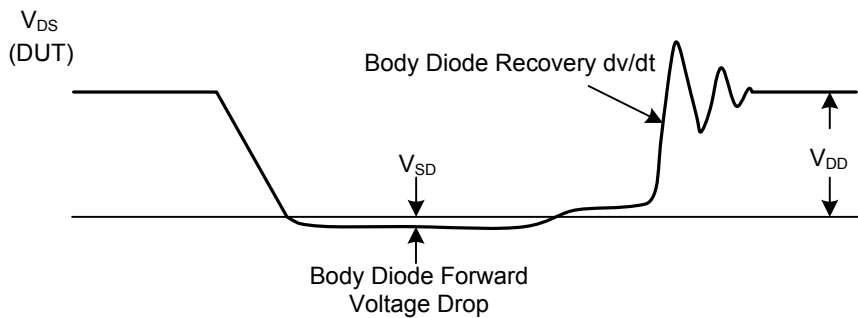
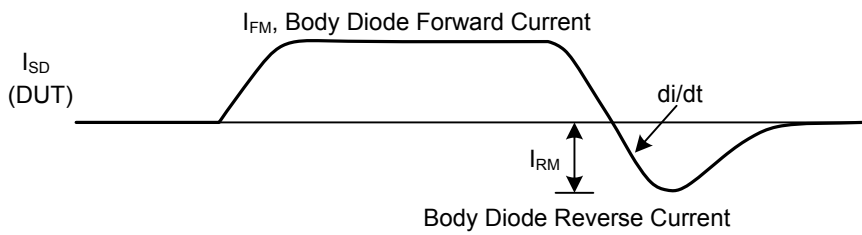
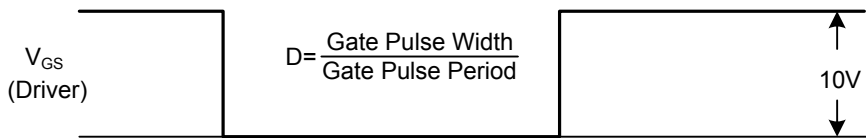
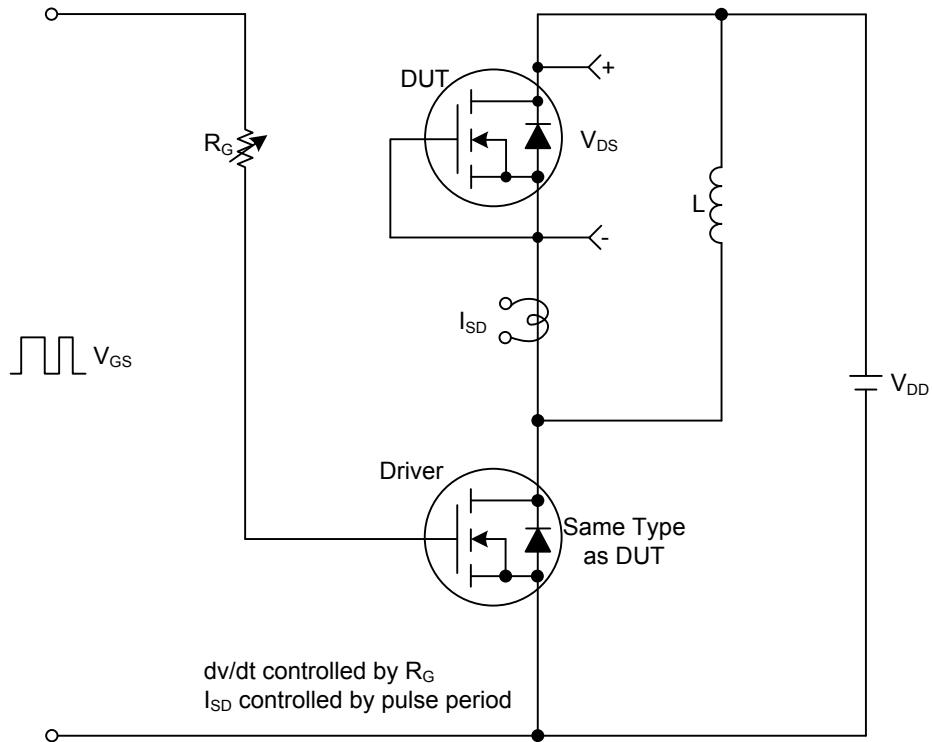
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---------------------|---|-----|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 200 | | | V |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =200V, V _{GS} =0V | | | 1 | μA |
| Gate-Source Leakage Current | I _{GSS} | V _{GS} =±25V, V _{DS} =0V | | | ±10 | μA |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | V _{DS} = V _{GS} , I _D =250μA | 2.0 | | 4.0 | V |
| Static Drain-Source On-Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =3.5A | | 0.58 | 0.69 | Ω |
| DYNAMIC PARAMETERS | | | | | | |
| Input Capacitance | C _{ISS} | V _{DS} =25V, V _{GS} =0V, f=1.0MHz | | 190 | 250 | pF |
| Output Capacitance | C _{OSS} | | | 60 | 75 | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | 10 | 13 | pF |
| SWITCHING PARAMETERS | | | | | | |
| Total Gate Charge | Q _G | V _{GS} =10V, V _{DS} =100V, I _D =7A (Note 1,2) | | 5.8 | 7.5 | nC |
| Gate Source Charge | Q _{GS} | | | 1.4 | | nC |
| Gate Drain Charge | Q _{GD} | | | 2.5 | | nC |
| Turn-ON Delay Time | t _{D(ON)} | V _{DD} =50V, I _D =7A, R _G =25Ω (Note 1,2) | | 7 | 25 | ns |
| Turn-ON Rise Time | t _R | | | 24 | 60 | ns |
| Turn-OFF Delay Time | t _{D(OFF)} | | | 13 | 35 | ns |
| Turn-OFF Fall-Time | t _F | | | 19 | 50 | ns |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | | | | 7 | A |
| Maximum Pulsed Drain-Source Diode Forward Current | I _{SM} | | | | 28 | A |
| Drain-Source Diode Forward Voltage | V _{SD} | I _S =7A, V _{GS} =0V | | | 1.5 | V |

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

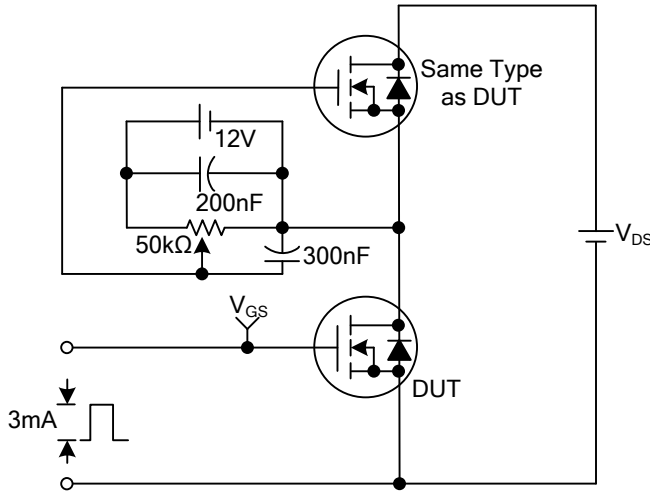
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

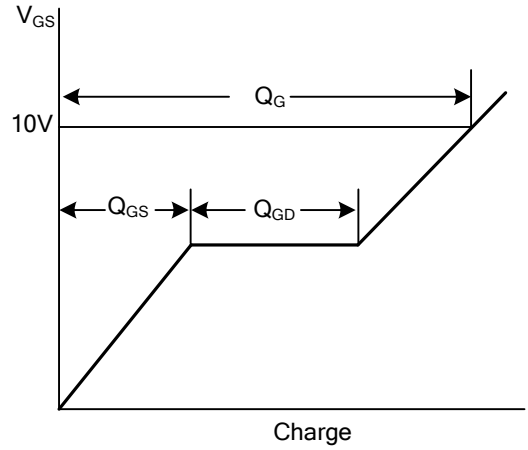
Peak Diode Recovery dv/dt Test Circuit & Waveforms



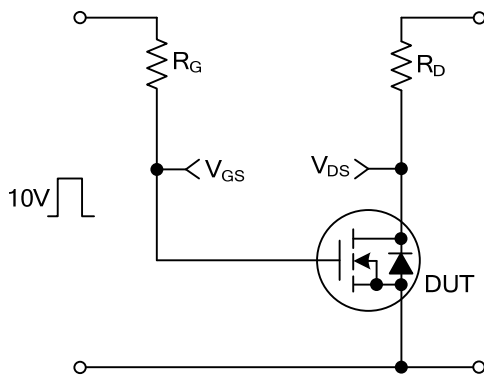
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



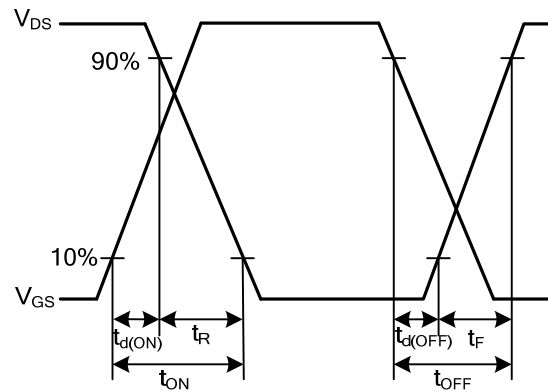
Gate Charge Test Circuit



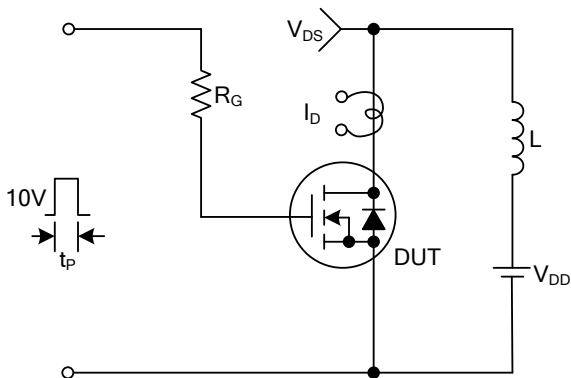
Gate Charge Waveforms



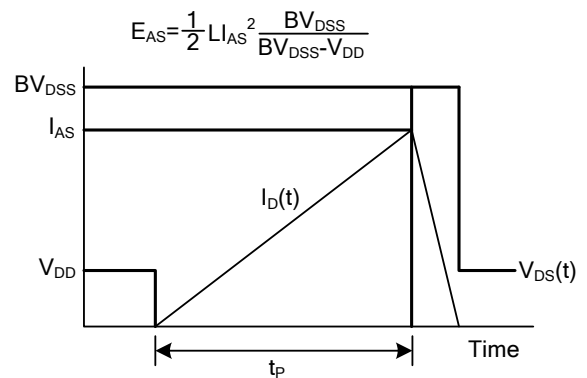
Resistive Switching Test Circuit



Resistive Switching Waveforms

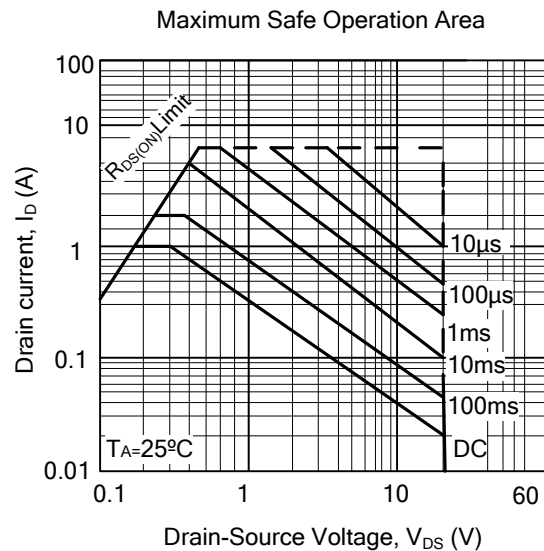
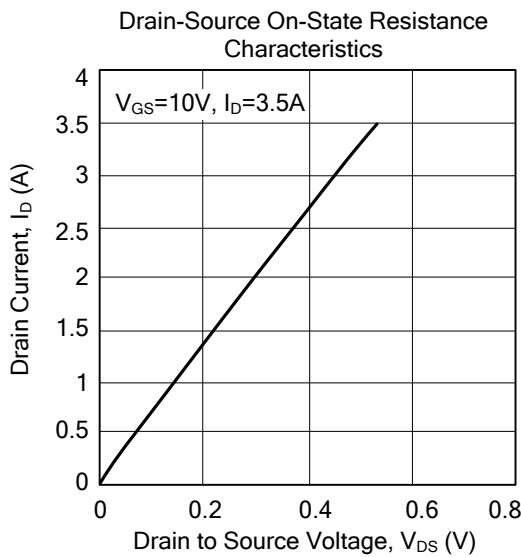
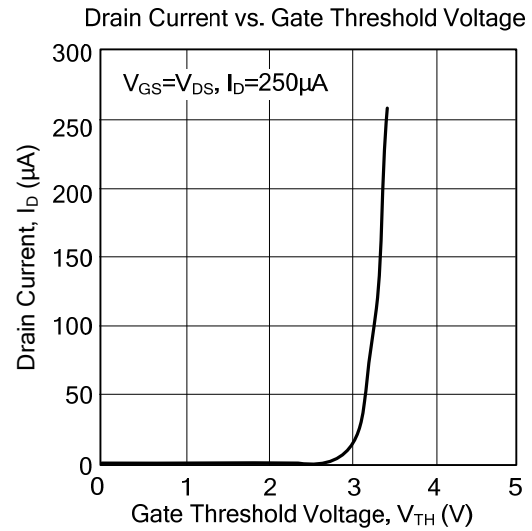
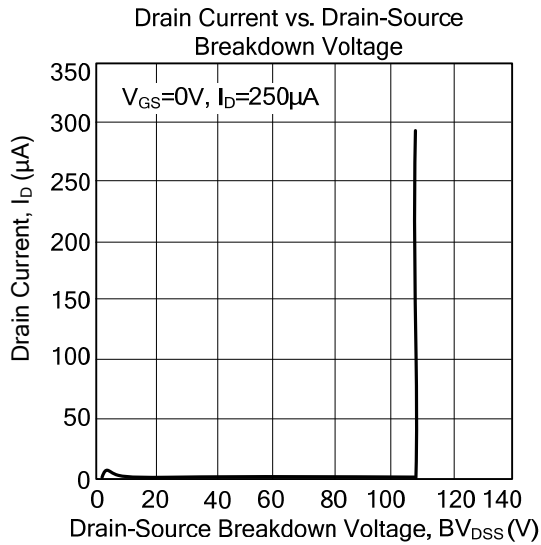


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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